TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K04FV

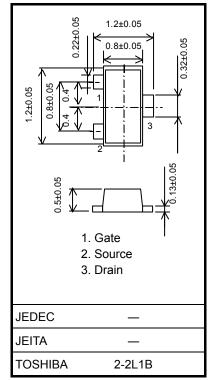
High Speed Switching Applications

- With built-in gate-source resistor: R_{GS} = 1 MΩ (typ.)
- 2.5 V gate drive
- High input impedance
- Low gate threshold voltage: Vth = 0.7~1.3 V
- Optimum for high-density mounting in small packages

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DS}	20	V
Gate-source voltage	V _{GSS}	10	V
DC drain current	I _D	100	mA
Drain power dissipation (Ta = 25° C)	P _D (Note 1)	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C

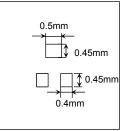
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 1.5 mg (typ.)

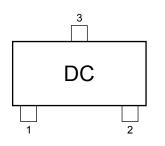
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

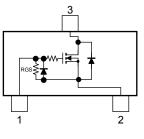
Note 1: Total rating, mounted on FR4 board (25.4 mm \times 25.4 mm \times 1.6 t)



Marking

Equivalent Circuit



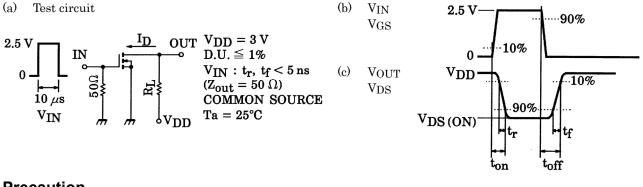


Unit: mm

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0$	_		15	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	nt	I _{DSS}	$V_{DS}=20~V,~V_{GS}=0$			1	μA
Gate threshold vol	tage	V _{th}	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.7		1.3	V
Forward transfer a	dmittance	Y _{fs}	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	25	50		mS
Drain-source on-resistance		R _{DS (ON)}	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		4	12	Ω
Input capacitance		C _{iss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		11.0		pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$		3.3		pF
Output capacitance		C _{oss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		9.3		pF
Switching time	Turn-on time	t _{on}	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 \sim 2.5 \text{ V}$		0.16		μS
	Turn-off time	t _{off}	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 \sim 2.5 \text{ V}$	_	0.19		
Gate-source resistor		R _{GS}	V _{GS} = 0~10 V	0.7	1.0	1.3	MΩ

Switching Time Test Circuit

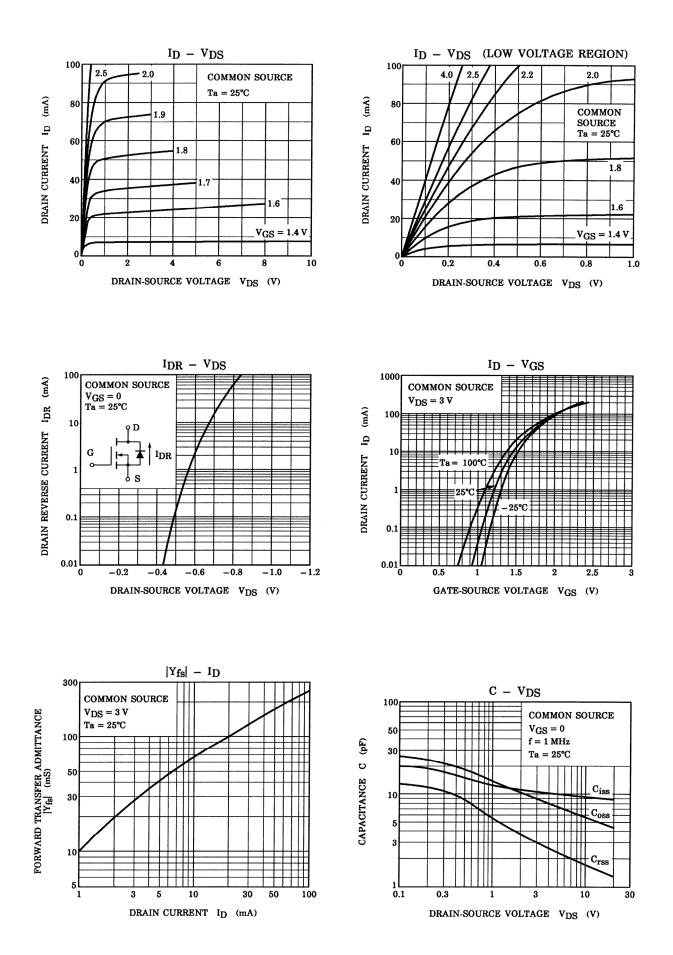


Precaution

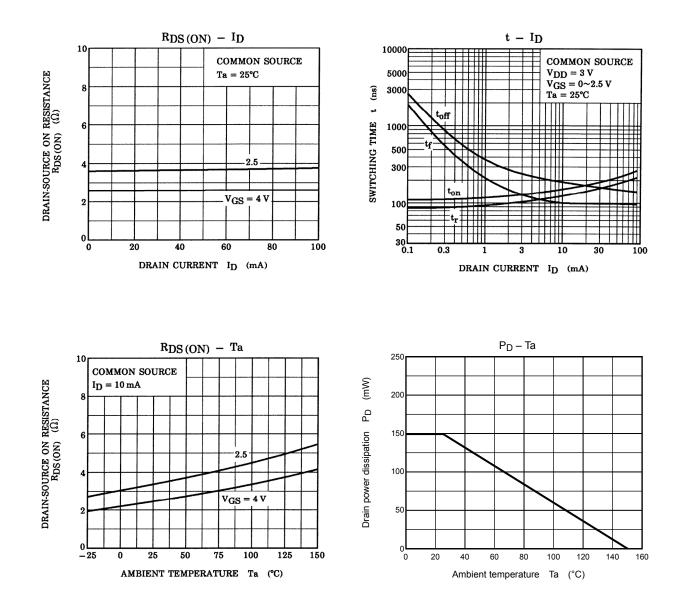
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 100 \ \mu A$ for this product. For normal switching operation, $V_{GS \ (on)}$ requires a higher voltage than V_{th} and $V_{GS \ (off)}$ requires a lower voltage than V_{th} .

(The relationship can be established as follows: V_{GS (off)} < V_{th} < V_{GS (on)}) Take this into consideration when using the device.

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